

# GL4910

## Side View Type Infrared Emitting Diode for Camera AF (Automatic Focusing)

### ■ Features

1. Small spot light diameter for easy beam diaphragming  
(\*Apparent emission diameter : TYP.  $\phi$  0.32 mm)
2. Uniform emission intensity on chip emitting surface
3. Low peak forward voltage type  
(Peak forward voltage  $V_{FM}$ : TYP. 1.7V)

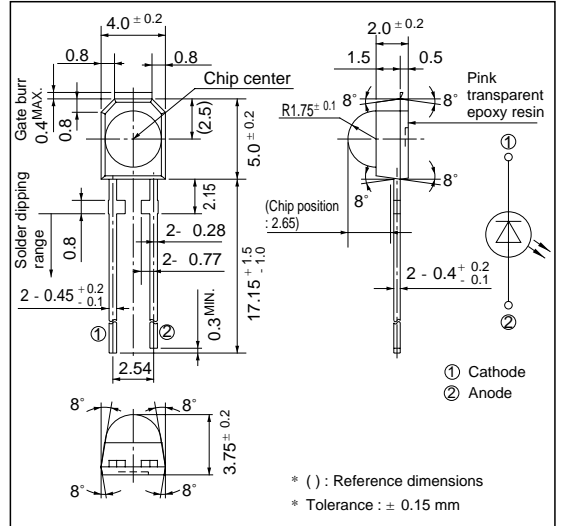
\* Expansion range on lens surface of infrared emitted from chips

### ■ Applications

1. Cameras

### ■ Outline Dimensions

(Unit : mm)



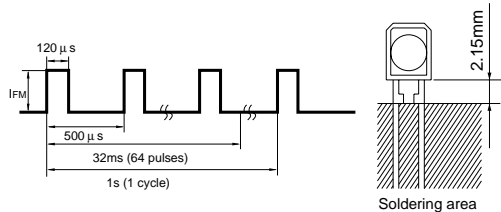
### ■ Absolute Maximum Ratings

( $T_a=25^\circ\text{C}$ )

| Parameter                           | Symbol    | Rating       | Unit             |
|-------------------------------------|-----------|--------------|------------------|
| Forward current                     | $I_F$     | 50           | mA               |
| <sup>*1</sup> Peak forward current  | $I_{FM}$  | 1            | A                |
| Reverse voltage                     | $V_R$     | 4            | V                |
| Operating temperature               | $T_{opr}$ | - 25 to + 60 | $^\circ\text{C}$ |
| Storage temperature                 | $T_{stg}$ | - 40 to + 85 | $^\circ\text{C}$ |
| <sup>*2</sup> Soldering temperature | $T_{sol}$ | 260          | $^\circ\text{C}$ |

<sup>\*1</sup> 30,00 cycles max. on pulse conditions shown in the right drawing

<sup>\*2</sup> For 5 seconds at the position of 2.15 mm from the resin edge



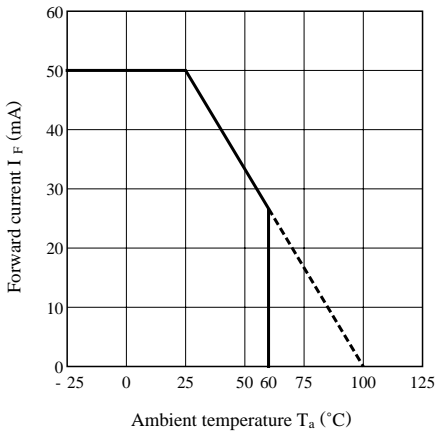
**Electro-optical Characteristics**

(Ta=25 °C)

| Parameter                 | Symbol           | Conditions                               | MIN. | TYP.     | MAX. | Unit          |
|---------------------------|------------------|--|------|----------|------|---------------|
| Forward voltage           | $V_F$            | $I_F = 50\text{mA}$                      | -    | 1.55     | 1.7  | V             |
| Peak forward voltage      | $V_{FM}$         | $I_{FM} = 300\text{mA}, t = 10\text{ms}$ | -    | 1.7      | 1.95 | V             |
| Reverse current           | $I_R$            | $V_R = 1\text{V}$                        | -    | -        | 100  | $\mu\text{A}$ |
| Radiant flux              | ${}^*3 \Phi_e$   | $I_{FM} = 300\text{mA}, t = 10\text{ms}$ | 4.2  | 9        | -    | mW            |
| Peak emission wavelength  | $\lambda_p$      | $I_F = 50\text{mA}$                      | -    | 850      | -    | nm            |
| Half intensity wavelength | $\Delta \lambda$ | $I_F = 50\text{mA}$                      | -    | 35       | -    | nm            |
| Half intensity angle      | $\Delta \theta$  | $I_F = 50\text{mA}$                      | -    | $\pm 32$ | -    | $^\circ$      |
| Terminal capacitance      | $C_t$            | $V_R = 0, f = 1\text{MHz}$               | -    | 80       | -    | pF            |

\*3 Emission output to effective angle  $\pm 25^\circ$

**Fig. 1 Forward Current vs. Ambient Temperature**



**Fig. 2 Peak Forward Current vs. Duty Ratio**

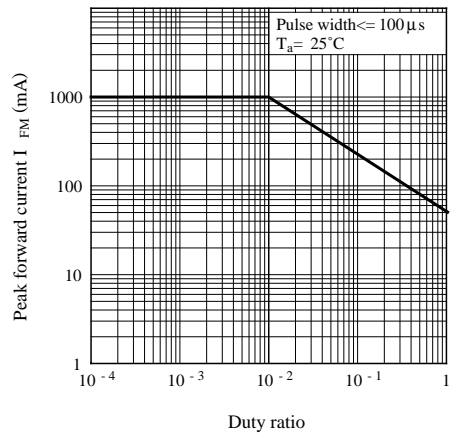


Fig. 3 Spectral Distribution

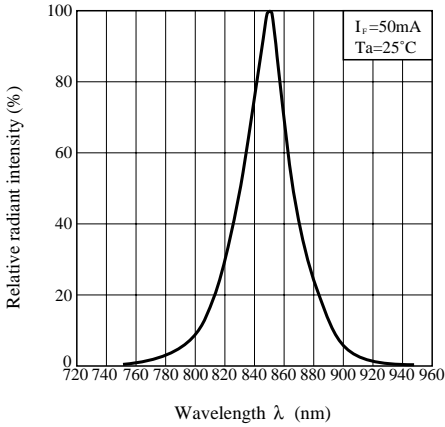


Fig. 4 Peak Emission Wavelength vs. Ambient Temperature

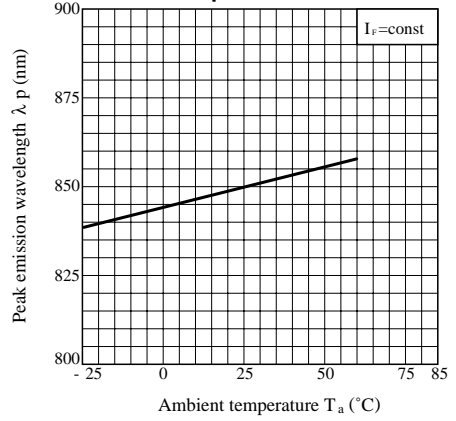


Fig. 5 Forward Current vs. Forward Voltage

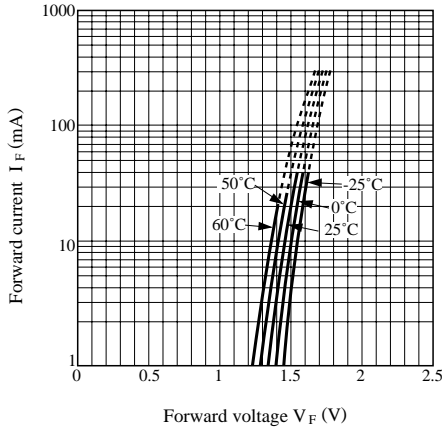


Fig. 6 Relative Radiant Flux vs. Ambient Temperature

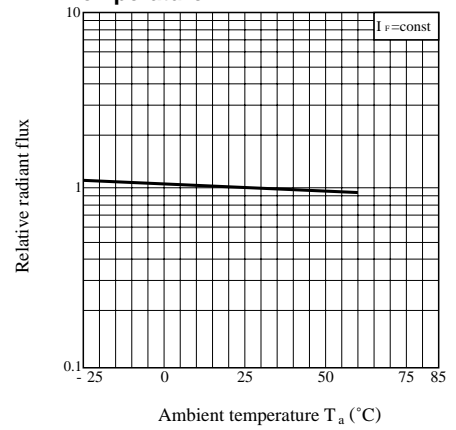


Fig. 7 Radiant Flux vs. Forward Current

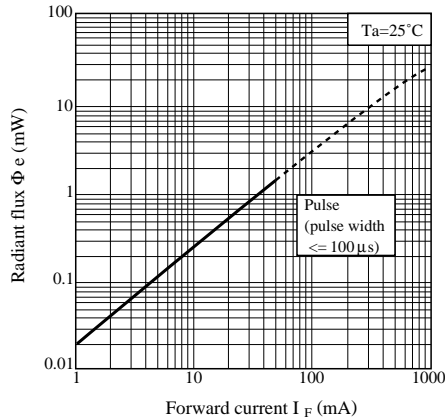
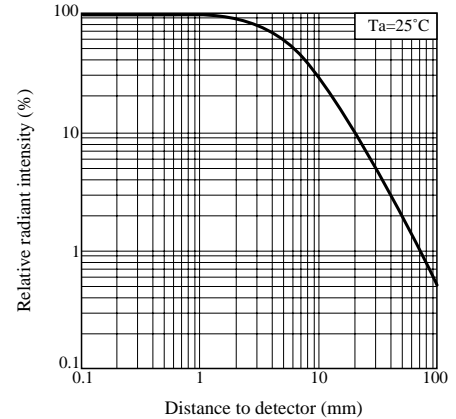
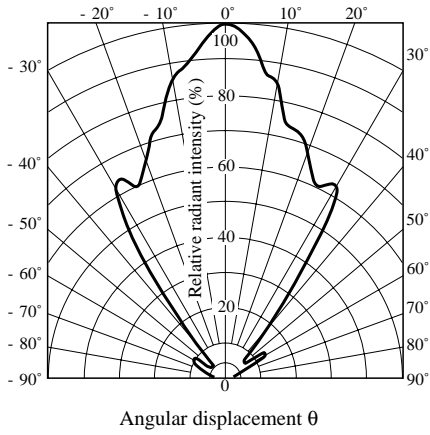


Fig. 8 Relative Radiant Intensity vs. Distance



**Fig. 9 Radiation Diagram** $(T_a = 25^\circ\text{C})$ 

- Please refer to the chapter "Precautions for Use". (Page 78 to 93)